

Form 1449*	Atty. Docket No.: 303.354US2	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	09/135,413
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
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Sheet 1 of 1

Form 1449*	Atty. Docket No.: 303.354US2	Serial No. 09/135,413
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: August 14, 1998	Group: 2818

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VS	4,460,670	07/01/1984	Ogawa, et al.	430	57	
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VS	5,145,741	09/01/1992	Quick	428	402	
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VS	5,740,104	04/14/1998	Forbes, L.	365	185.03	01/29/97
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**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
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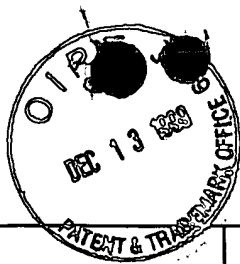
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Form 1449*

Atty. Docket No.: 303.354US2

Serial No. 09/135,413

INFORMATION DISCLOSURE STATEMENT
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Applicant: Leonard Forbes et al.

Filing Date: August 14, 1998

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**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
VN	5,049,950	09/17/1991	Fujii, Y., et al.	357	2	08/09/90
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VN	Sakata, I., et al., "Amorphous Silicon/Amorphous Silicon Carbide Heterojunctions Applied to Memory Device Structures", <u>Electronics Letters</u> , 30(9), pp. 688-689, (April 28, 1994)					
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V. NGUYEN

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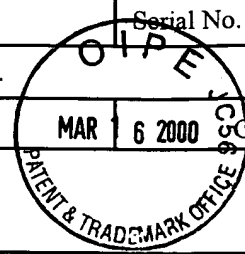
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	Filing Date: August 14, 1998	



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VN		5,235,195	08/10/1993	Tran, N.T., et al.	257	59	10/19/92
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Initial							Yes	No

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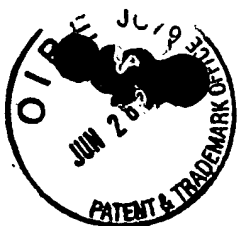
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**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
VN	5,886,368	03/23/1999	Forbes, L., et al.	257	77	07/29/97
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